ABSTRACT

The present invention provides a substrate treatment method comprising the following steps: continuously rotating a substrate; a first nozzle continuously spraying water above the central region of the substrate; during the substrate cleaning process, the first nozzle starting moving from a first central position in the central region of the substrate to a first edge position in the edge region of the substrate, and a second nozzle starting spraying a chemical solution onto the rotating substrate and moving from a second edge position in the edge region of the substrate to a second central position in the central region of the substrate; the first nozzle and the second nozzle performing staggered reciprocating movement between the central region and the edge region of the substrate until the substrate cleaning process is completed; after the substrate cleaning process is completed, the second nozzle stopping spraying the chemical solution, and the first nozzle continuing to spray water and returning to the central region of the substrate. The substrate treatment method and the substrate treatment apparatus of the present invention continuously spray water during the substrate treatment process, ensuring the integrity of the liquid film coverage on the substrate surface and avoiding the risk of water mark formation caused by bare silicon being exposed in the chamber.